L Number		Search Text	DB	Time stamp
9	655258	H01L\$4	EPO; JPO;	2003/05/05 02:11
			DERWENT	
10	366362	H01L\$4 and semiconductor	EPO; JPO;	2003/05/05 02:1
			DERWENT	
11	523	(H01L\$4 and semiconductor) and (self adj	EPO; JPO;	2003/05/05 02:1
-	020	aligned adj contact)	DERWENT	2003, 03, 00 02.1
2	2	((H01L\$4 and semiconductor) and (self adj	EPO; JPO;	2003/05/05 02:10
-2	2		1	1 2003/03/03 02.10
		aligned adj contact)) and (stopping adj	DERWENT	
	1740	layer)		0000 /05 /05 00 0
15	1748		USPAT	2003/05/05 02:20
		align) adj (contact or contacts)	:	
16	67	(self adj (aligned or aligning or aligns	USPAT	2003/05/05 02:42
		or align) adj (contact or contacts)) and		
1		((dry adj etch\$3) with (interdielectric or		
		dielectric))		
.7	0	planarizing with (gate adj upper adj	USPAT	2003/05/05 02:4
		dielectric)	}	
.8	0	ţ.	USPAT	2003/05/05 02:41
	· ·	dielectric)		
L9	0	planar\$5 with (gate adj upper adj	USPAT	2003/05/05 02:41
	U		USIAI	2003/03/03 02.40
	1	dielectric)	HCDAM	2002/05/05 00:4
0		gate adj upper adj dielectric	USPAT	2003/05/05 02:44
21		gate adj dielectric	USPAT	2003/05/05 02:44
2	33	planarizing with (gate adj dielectric)	USPAT	2003/05/05 02:45
23	8	planarize with (gate adj dielectric)	USPAT	2003/05/05 02:48
4	157		USPAT	2003/05/05 02:48
25	120	(planar\$5 with (gate adj dielectric)) not	USPAT	2003/05/05 02:48
		((planarize with (gate adj dielectric)) or		
		(planarizing with (gate adj dielectric)))		
29	0	(("6313018") or ("6287957") or ("6165901")	USPAT	2003/05/05 03:42
29	8		USPAI	2003/03/03 03:42
		or ("6204161") or ("6507064") or	į	
ļ		("6468859") or ("6380042") or		
ł		("6081016")).PN.		•
- j	5927	(gate adj electrode) and ((dry adj	USPAT	2003/05/03 21:10
i		etching) or CMP or (chemical adj	ŀ	•
		mechanical adj polishing))	i i	:
_ 1	19	(gate adj electrode) and (interdielectric)	USPAT	2002/06/30 17:5
	10	and ((dry adj etching) or CMP or (chemical	001111	2002,00,00 1:00
		and ((dry adj etching) of cmr of (chemical adj mechanical adj polishing))	; ŧ	
	2.1		HCDAM	2002/06/30 18:03
-	31	(gate) and (interdielectric) and ((dry adj	USPAT	2002/06/30 18:0.
		etching) or CMP or (chemical adj		
		mechanical adj polishing))		
-	1945	438/586.ccls. or 438/587.ccls. or	USPAT	2003/04/16 15:03
		438/595.ccls. or 438/597.ccls. or		
		438/598.ccls.		
-	214	438/584.ccls.	USPAT	2003/04/16 15:02
.	1650	438/666.ccls. or 438/669.ccls. or	USPAT	2003/05/05 02:1
	1000	438/674.ccls. or 438/684.ccls. or	1	3333, 33, 33 34.1
		438/685.ccls.		
	1701		HEDAT	2003/05/05 03:1
	1791	(438/586.ccls. or 438/587.ccls. or	USPAT	2003/03/03 03:1
		438/595.ccls. or 438/597.ccls. or		
		438/598.ccls.) not (438/584.ccls. or		
		(438/666.ccls. or 438/669.ccls. or		
		438/674.ccls. or 438/684.ccls. or		!
		438/685.ccls.))		
	175	438/584.ccls. not ((438/586.ccls. or	USPAT	2003/04/16 15:5
and the same of th	1/3	438/587.ccls. or 438/595.ccls. or	. 552111	:
			İ	1
!		438/597.ccls. or 438/598.ccls.) or		
1		(438/666.ccls. or 438/669.ccls. or		
í		438/674.ccls. or 438/684.ccls. or		
4		438/685.ccls.))		
	1514	(438/666.ccls. or 438/669.ccls. or	USPAT	2003/04/16 16:5
		438/674.ccls. or 438/684.ccls. or		
1		438/685.ccls.) not ((438/586.ccls. or		
		438/587.ccls. or 438/595.ccls. or		
		430/307.CCIS. OF 430/393.CCIS. OF		
		438/597.ccls. or 438/598.ccls.) or		
-		438/584.ccls.)		1 0000 /05 /00 00 5
	290389	gate	USPAT	2003/05/03 21:1
			LICDAM	1 2002 /05 /02 21.4
	21471	<pre>gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))</pre>	USPAT	2003/05/03 21:4

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-	13415	with (nitride or (silicon adj nitride))))	USPAT	2003/05/03 21:21
_	1564	and (dielectric or interdielectric) ((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz\$3 with ((dry adj etching) or CMP))	USPAT	2003/05/03 21:22
	630	1 ' '	USPAT	2003/05/03 21:39
_	89		USPAT	2003/05/03 21:23
	541		USPAT	2003/05/03 21:46
_	21	, <u>-</u>	USPAT	2003/05/03 21:48
	1665		USPAT	2003/05/03 21:54